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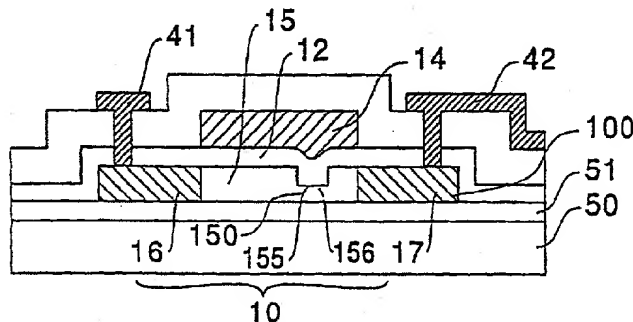
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(54) Title: A THIN FILM TRANSISTOR AND A METHOD FOR MANUFACTURING THEREOF



(57) Abstract: In TFT (10), the channel region (15) towers over the gate electrode (14) through the gate insulation film (12), the source region (16) connecting to the channel (15) and the drain region (17) connecting to the channel region (15) on the opposite side of the source region (16) are formed on the polycrystalline semiconductor film (100) on which island-like patterning is performed. An indented section (155) is formed on the surface of the channel region (15), and the section corresponding to the indented section (155) becomes the recombination center (150) which captures the small-number carrier (holes) because

the degree of the crystallization is low in the section corresponding to the indented section (155) due to shift from the optimum conditions at the time of laser annealing of the semiconductor (100). Thus the invention provides a TFT and its production method which enable the stabilizing of saturation current and improving reliability by improving the film quality of the channel region.

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